

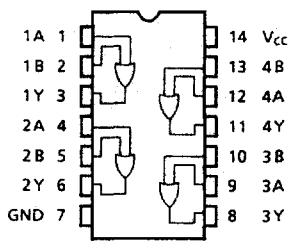
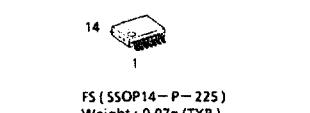
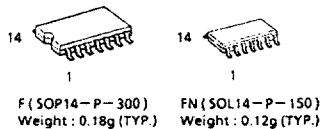
QUAD 2 - Input OR Gate

The TC74LVQ32 is a high speed CMOS 2-INPUT OR GATE fabricated with silicon gate and double-layer metal wiring C²MOS technology.

Designed for use in 3.3 Volt systems, it achieves high speed operation while maintaining the CMOS low power dissipation. The internal circuit is composed of 2 stages including buffer output, which provide high noise immunity and stable output. All inputs are equipped with protection circuits against static discharge or transient excess voltage.

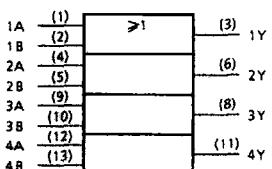
Features

- High Speed: $t_{pd} = 4.1\text{ns}$ (Typ.) at $V_{CC} = 3.3\text{V}$
- Low Power Dissipation: $I_{CC} = 2.5\mu\text{A}$ (Max.) at $T_a = 25^\circ\text{C}$
- Input Voltage Level:
 - $V_{IL} = 0.8\text{V}$ (Max.) at $V_{CC} = 3\text{V}$
 - $V_{IH} = 2.0\text{V}$ (Min.) at $V_{CC} = 3\text{V}$
- Symmetrical Output Impedance: $|I_{OHL}| = I_{OL} = 12\text{mA}$ (Min.)
- Balanced Propagation Delays: $t_{PLH} = t_{PHL}$
- Pin and Function Compatible with 74HC32



(TOP VIEW)

Pin Assignment



IEC Logic Symbol

Truth Table

Inputs		Outputs
A	B	Y
L	L	L
L	H	H
H	L	H
H	H	H

Absolute Maximum Ratings

Parameter	Symbol	Value	Unit
Supply Voltage Range	V _{CC}	-0.5 ~ 7.0	V
DC Input Voltage	V _{IN}	-0.5 ~ V _{CC} + 0.5	V
DC Output Voltage	V _{OUT}	-0.5 ~ V _{CC} + 0.5	V
Input Diode Current	I _{IK}	±20	mA
Output Diode Current	I _{OK}	±50	mA
DC Output Current	I _{OUT}	±50	mA
DC V _{CC} /Ground Current	I _{CC}	±100	mA
Power Dissipation	P _D	180	mW
Storage Temperature	T _{STG}	-65 ~ 150	°C
Lead Temperature 10sec	T _L	300	°C

Recommended Operating Conditions

Parameter	Symbol	Value	Unit
Supply Voltage	V _{CC}	2.0 ~ 3.6	V
Input Voltage	V _{IN}	0 ~ V _{CC}	V
Output Voltage	V _{OUT}	0 ~ V _{CC}	V
Operating Temperature	T _{OPR}	-40 ~ 85	°C
Input Rise and Fall Time	dt/dv	0 ~ 100	ns/V

DC Electrical Characteristics

Parameter	Symbol	Test Condition	V _{CC} (V)	Ta = 25°C			Ta = -40 ~ 85°C		Unit
				Min.	Typ.	Max.	Min.	Max.	
High-Level Input Voltage	V _{IH}	—	3.0	2.0	—	—	2.0	—	V
Low-Level Input Voltage	V _{IL}	—	3.0	—	—	0.8	—	0.8	
High-Level Output Voltage	V _{OH}	V _{IN} = V _{IH} or V _{IL} I _{OH} = -50μA I _{OH} = -12mA	3.0 3.0	2.9 2.58	3.0 —	— —	2.9 2.48	— —	
Low-Level Output Voltage	V _{OL}	V _{IN} = V _{IL} I _{OL} = 50μA I _{OL} = 12mA	3.0 3.0	— —	0.0 —	0.1 0.36	— —	0.1 0.44	
Input Leakage Current	I _{IN}	V _{IN} = V _{CC} or GND	3.6	—	—	±0.1	—	±1.0	
Quiescent Supply Current	I _{CC}	V _{IN} = V _{CC} or GND	3.6	—	—	2.5	—	25.0	μA

AC Electrical Characteristics (Input $t_r = t_f = 3\text{ns}$, $C_L = 50\text{pF}$, $R_L = 500\Omega$)

Parameter	Symbol	Test Condition	V_{CC} (V)	Ta = 25°C			Ta = -40 ~ 85°C		Unit
				Min	Typ.	Max.	Min.	Max.	
Propagation Delay Time	t_{PLH} t_{PHL}	(Note 1)	2.7 3.3±0.3	— —	5.4 4.5	12.7 9.0	1.0 1.0	15.0 10.0	ns
Output to Output Skew	t_{osLH} t_{osHL}		2.7 3.3±0.3	— —	— —	1.5 1.5	— —	1.5 1.5	
Input Capacitance	C_{IN}	(Note 2)		—	5	10	—	10	pF
Power Dissipation Capacitance	C_{PD}	(Note 3)		—	24	—	—	—	

Note (1) Parameter guaranteed by design. $t_{osLH} = |t_{PLHm} - t_{PLHn}|$, $t_{osHL} = |t_{PHLm} - t_{PHLn}|$

Note (2) Parameter guaranteed by design.

Note (3) C_{PD} is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption.

Average operating current can be obtained by the equation:

$$I_{CC}(\text{opr}) = C_{PD} \cdot V_{CC} \cdot f_{IN} + I_{CC}/4 \text{ (per Gate)}$$

Noise Characteristics (Input $t_r = t_f = 3\text{ns}$, $C_L = 50\text{pF}$, $R_L = 500\Omega$)

Parameter	Symbol	Test Condition	V_{CC}	Ta = 25°C		Unit
				Typ.	Max.	
Quiet Output Maximum Dynamic V_{OL}	V_{OLP}	—	3.3	0.3	0.8	V
Quiet Output Minimum Dynamic V_{OL}	V_{OLV}	—	3.3	-0.3	-0.8	V
Minimum High Level Dynamic Input Voltage	V_{IHd}	—	3.3	—	2.0	V
Maximum Low Level Dynamic Input Voltage	V_{ILd}	—	3.3	—	0.8	V

Notes

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